Elektronische Bauelemente

SSG23N06SV-C

23A, 60V, $R_{DS(ON)}$ 3.8mΩ

N-Channel Shielded Gate Trench Power MOSFET

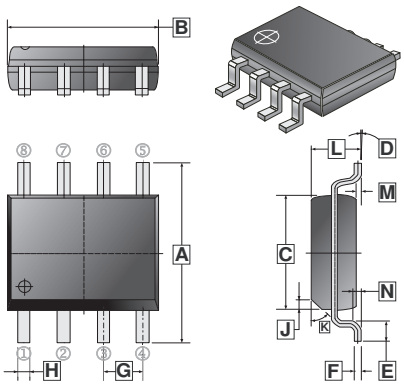
RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

DESCRIPTION

The SSG23N06SV-C is the Shielded Gate Technology N-Ch MOSFETs with extreme high cell density, which provide excellent $R_{DS(ON)}$ and gate charge for most of the synchronous buck converter applications.

The SSG23N06SV-C meet the RoHS and Green Product requirement with full function reliability approved.

SOP-8



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	5.79	6.20	H	0.33	0.51
B	4.70	5.11	J	0.375 REF.	
C	3.80	4.00	K	45°REF.	
D	0°	8°	L	1.3	1.752
E	0.40	1.27	M	0	0.25
F	0.10	0.25	N	0.25 REF.	
G	1.27 TYP.				

FEATURES

- Shielded Gate Trench Technology
- Super Low Gate Charge
- Green Device Available

MARKING

23N06SV
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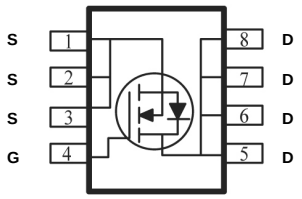

PACKAGE INFORMATION

Package	MPQ	Leader Size
SOP-8	2.5K	13' inch

ORDER INFORMATION

Part Number	Type
SSG23N06SV-C	Lead (Pb)-free and Halogen-free

ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise specified)

Parameter		Symbol	Ratings	Unit
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current [1] @V_{GS}=10V	T_A=25℃	I_D	23	A
	T_A=70℃		18	
Pulsed Drain Current [2 3]		I_{DM}	60	A
Power Dissipation [2]	T_A=25℃	P_D	3.1	W
Operating Junction & Storage Temperature Range		T_J, T_{STG}	-55~150	℃
Thermal Resistance Ratings				
Thermal Resistance Junction-ambient [1]		$R_{\theta JA}$	t≦10s, 40	℃/W
			Steady State, 75	
Thermal Resistance Junction-Case [1]		$R_{\theta JC}$	24	

ELECTRICAL CHARACTERISTICS (T_J=25℃ unless otherwise specified)

Parameter		Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-Source Breakdown Voltage		BV_{DSS}	60	-	-	V	V_{GS}=0V, I_D=250μA
Gate-Threshold Voltage		$V_{GS(th)}$	2	-	4	V	V_{DS}=V_{GS}, I_D=250μA
Forward Transfer conductance		g_{fs}	-	65	-	S	V_{DS}=5V, I_D=10A
Gate-Source Leakage Current		I_{GSS}	-	-	±100	nA	V_{GS}= ±20V
Drain-Source Leakage Curren	T_J=25℃	I_{DSS}	-	-	1	μA	V_{DS}=48V,V_{GS}=0V
	T_J=55℃		-	-	5		V_{DS}=48V,V_{GS}=0V
Static Drain-Source On-Resistance [3]		$R_{DS(ON)}$	-	3.2	3.8	mΩ	V_{GS}=10V, I_D=10A
			-	3.9	5.2		V_{GS}=7V, I_D=5A
Total Gate Charge		Q_g	-	59	-	nC	I_D=10A V_{DS}=30V V_{GS}=10V
Gate-Source Charge		Q_{gs}	-	15	-		
Gate-Drain (“Miller”) Charge		Q_{gd}	-	10	-		
Turn-On Delay Time		$T_{d(on)}$	-	20	-	nS	V_{DD}=30V I_D=10A V_{GS}=10V R_G=3Ω
Rise Time		T_r	-	9	-		
Turn-Off Delay Time		$T_{d(off)}$	-	60	-		
Fall Time		T_f	-	15	-		
Input Capacitance		C_{iss}	-	3509	-	pF	V_{GS}=0V V_{DS}=30V f=1MHz
Output Capacitance		C_{oss}	-	1175	-		
Reverse Transfer Capacitance		C_{rss}	-	68	-		
Source-Drain Diode							
Diode Forward Voltage [3]		V_{SD}	-	-	1.2	V	I_S=1A, V_{GS}=0V
Continuous Source Current [1]		I_S	-	-	23	A	
Pulsed Source Current [2 3]		I_{SM}	-	-	60	A	
Reverse Recovery Time		T_{rr}	-	24	-	nS	I_F=10A, dI/dt=100A/μs, T_J=25℃
Reverse Recovery Charge		Q_{rr}	-	85	-	nC	

Notes:
1. The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.
2. The power dissipation is limited by 150°C junction temperature.
3. The data tested by pulsed, pulse width≦300us, duty cycle≦2%.

CHARACTERISTICS CURVE

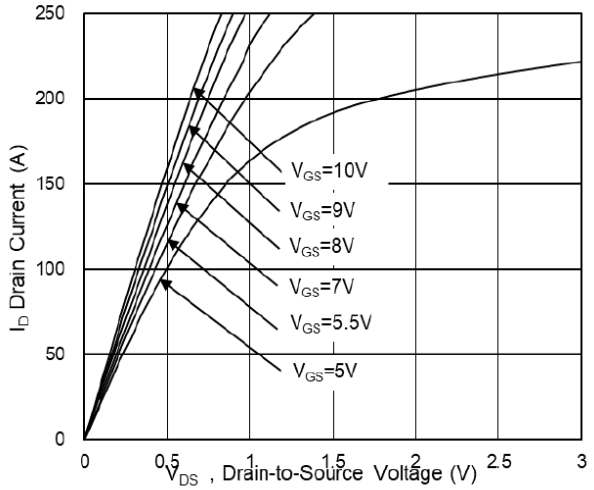

Fig.1 Typical Output Characteristics

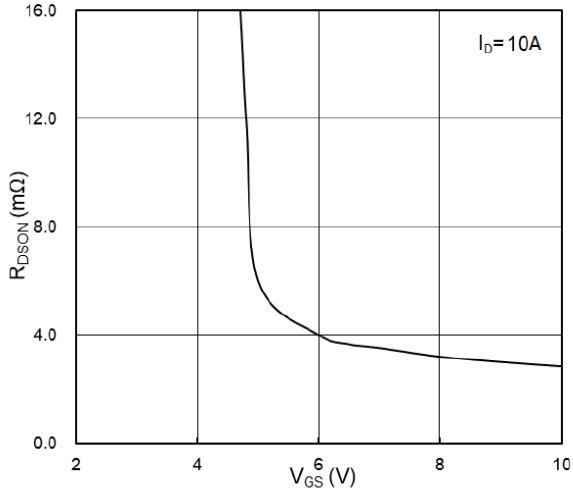

Fig.2 On-Resistance vs G-S Voltage

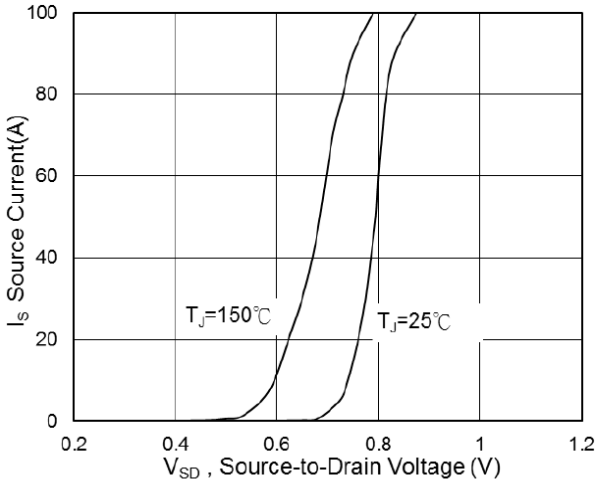

Fig.3 Diode Forward Voltage vs Current

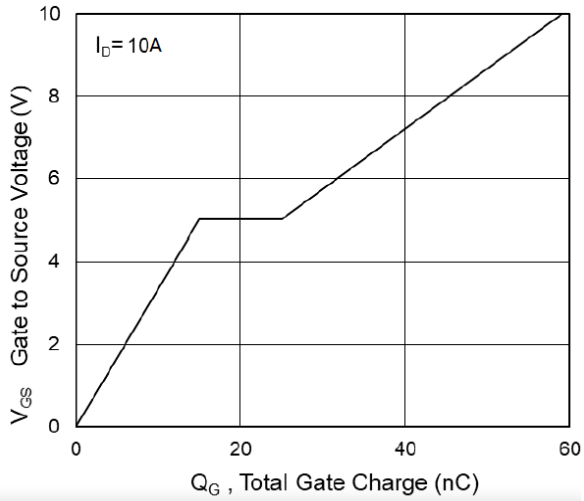

Fig.4 Gate-Charge Characteristics

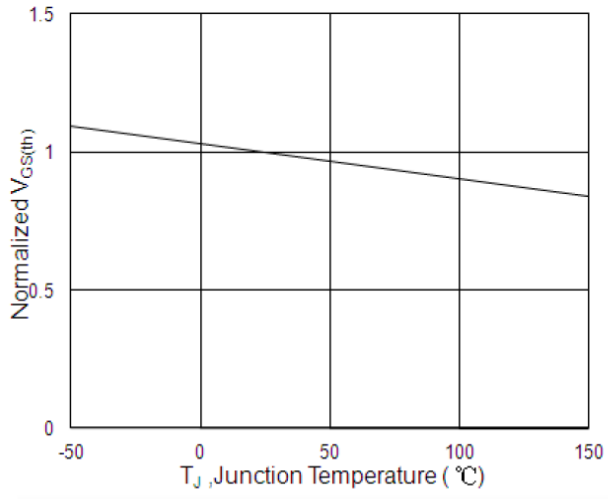

Fig.5 Normalized $V_{GS(th)}$ vs T_J

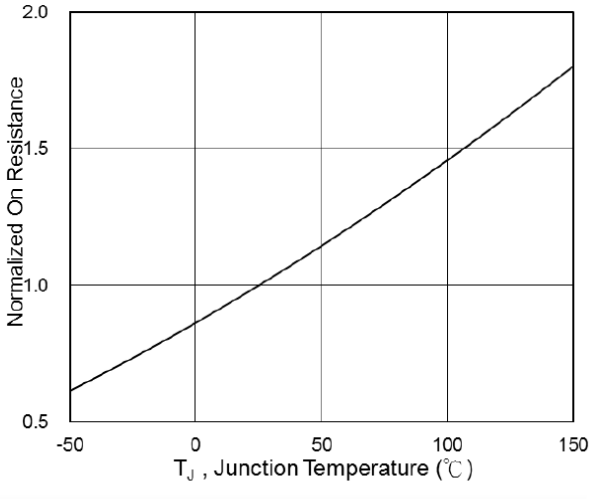

Fig.6 Normalized R_{DSON} vs T_J

CHARACTERISTICS CURVE

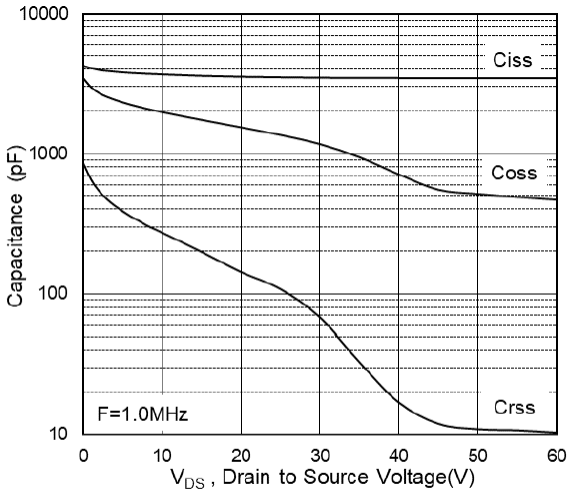

Fig.7 Capacitance

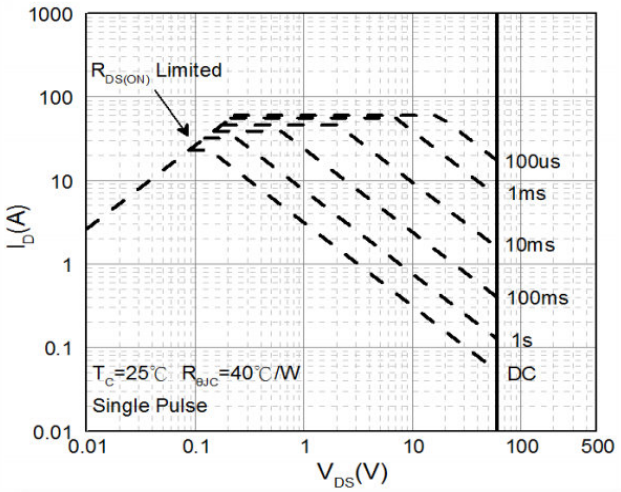

Fig.8 Safe Operating Area

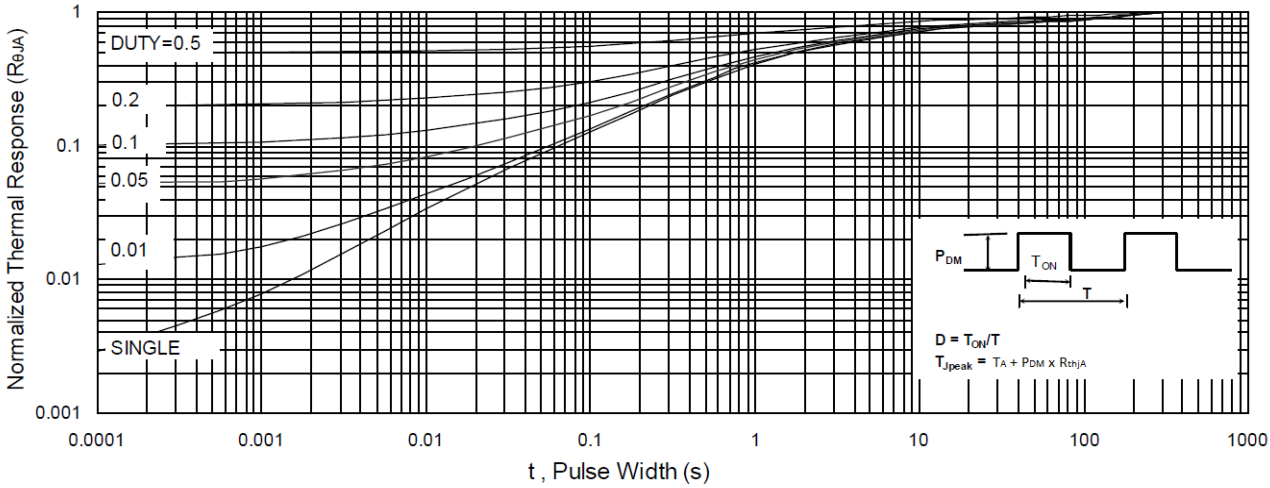

Fig.9 Normalized Maximum Transient Thermal Impedance

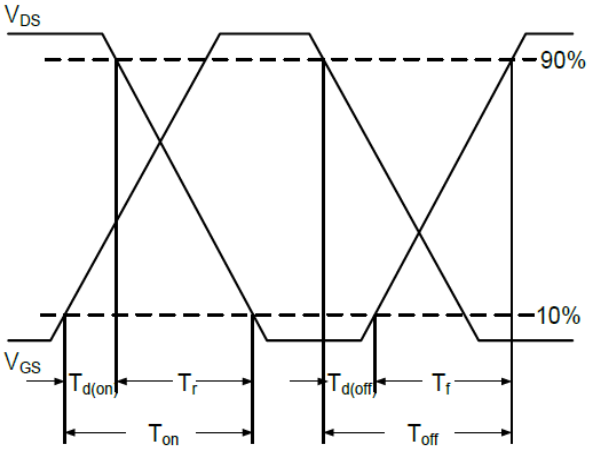

Fig.10 Switching Time Waveform

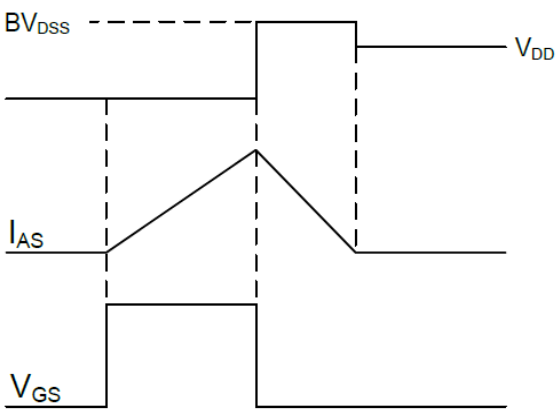

Fig.11 Unclamped Inductive Waveform